AMENDMENTS TO THE CLAIMS

1 to 5. **(Cancelled)**

6. **(New)** A high-brightness mechanoluminescence material consisting of a composite semiconductor crystal represented by the formula:

$$xM^1A^1 \cdot (1-x)M^2A^2$$

wherein M^1 is Mn or Eu, M^2 is Zn, Mn, Cd, Cu, Eu, Fe, Co, Ni, Mg or Ca, each of A^1 and A^2 is the same chalcogen with the proviso that M^1A^1 and M^2A^2 differ each from the other, and x is a positive number smaller than 1 and wherein the composite semiconductor crystal has a mixed structure of the wurtzite-type structure and the zincblende-type structure.

7. **(New)** A method for the preparation of the high-brightness mechanoluminescence material consisting of a composite semiconductor crystal represented by the formula:

$$xM^1A^1 \cdot (1-x)M^2A^2$$

wherein each of M^1 and M^2 is, independently from the other, an element selected from Zn, Mn, Cd, Cu, Eu, Fe, Co, Ni, Mg and Ca, each of A^1 and A^2 is an atom selected independently from chalcogens, with the proviso that M^1A^1 and M^2A^2 differ each from the other, and x is a positive number smaller than 1 and wherein the composite semiconductor crystal has a mixed structure of the wurtzite-type structure and the zincblende-type structure,

which comprises the steps of mixing source materials of the constituent ingredients; heating the thus obtained mixture in vacuum at a temperature lower than the sublimation point of the product to produce a composition represented by the formula

$$xM^1A^1 \cdot (1-x)M^2A^2$$

wherein each of M^1 and M^2 is, independently from the other, an element selected from Zn, Mn, Cd, Cu, Eu, Fe, Co, Ni, Mg and Ca, each of A^1 and A^2 is an atom selected independently from chalcogens and x is a positive number smaller than 1, with the proviso that M^1A^1 and M^2A^2 differ each from the other; causing sublimation of the composition at a temperature equal to or higher

than the sublimation point of the composition; and crystallizing the thus generated sublimate by condensation at a temperature lower than the sublimation point thereof.